



VMA70R850AD,VMD70R850AD,VMP70R850AD

N-CHANNEL POWER MOSFET

DESCRIPTION

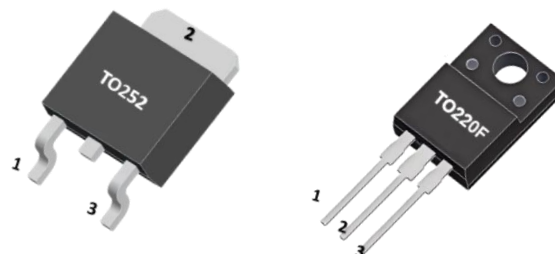
SJ-FET is new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance .This advanced technology has been tailored to minimize conduction loss , provide superior switching performance , and withstand extreme dv/dt rate and higher avalanche energy.SJ-FET is suitable for various AC/DC power conversion in switching mode operation for higher efficiency.

FEATURES

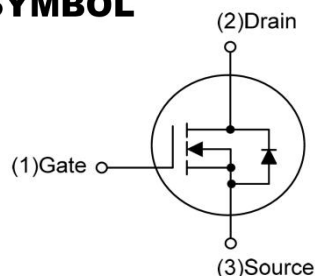
- * Very low FOM $R_{DS(on)} \times Q_g$
- * 100% avalanche tested
- * RoHS compliant

Applications

- * Uninterruptible Power Supply (UPS)
- * Power Factor Correction (PFC)
- * Charger



SYMBOL



ABSOLUTE MAXIMUM RATINGS(TA=25°C, unless otherwise specified.)

Parameter		Symbol	Value	Unit
Drain-Source Voltage (note2)		VDSS	700	V
Continuous Drain Current	TC = 25°C	ID	6	A
	TC = 100°C		3.3	
Pulsed Drain Current (note1)		IDM	24	A
Gate-Source Voltage		VGSS	±30	V
Single Pulse Avalanche Energy (note2)		EAS	53	mJ
Drain Source voltage slope (Vds=480V) (note3)		dV/dt	50	V/ns
Power Dissipation	TO-220F	PD	28	W
	TO-252		23	
Operating Junction and Storage Temperature Range		TJ, Tstg	-55~+150	°C



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■ THERMAL CHARACTERISTICS

Parameter		Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	TO-220F	RthJC	5.5	°C/W
	TO-252		4.4	
Thermal Resistance, Junction-to-Ambient	TO-220F	RthJA	62.5	
	TO-252		62	

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. VDD=50 V, VGS=10 V, L=10.8 mH, starting Tj=25 °C.

■ ELECTRICAL CHARACTERISTICS(unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Off&On Characteristics						
Drain-Source Breakdown Voltage	V(BR)DSS	VGS = 0V, ID = 250μA	700	--	--	V
Zero Gate Voltage Drain Current	IDSS	VDS = 700V, VGS = 0V TJ = 25°C	--	--	1	μA
		VDS = 700V, VGS = 0V TJ = 150°C	--	--	100	
Gate-Source Leakage Current	IGSS	VGS = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	VGS(th)	VDS = VGS, ID = 250μA	2.5	--	4.5	V
Drain-Source On-State-Resistance	RDS(on)	VGS = 10V, ID = 5.5A	--	780	940	mΩ
Dynamic&Switching Characteristics						
Input Capacitance	Ciss	VGS = 0V, VDS = 50V f = 1000KHz	--	360	--	pF
Output Capacitance	Coss		--	23	--	
Reverse Transfer Capacitance	Crss		--	2.8	--	
Total Gate Charge	Qg	VDD = 520V, ID = 4A VGS = 10V (Note 4)	--	7	--	nC
Gate-Source Charge	Qgs		--	1.5	--	
Gate-Drain Charge	Qgd		--	2.5	--	
Turn-on Delay Time	td(on)	VDD = 400V, ID = 4A RG = 25Ω , VGS = 10V	--	36	--	ns
Turn-on Rise Time	tr		--	27	--	
Turn-off Delay Time	td(off)		--	80	--	
Turn-off Fall Time	tf		--	30	--	
Drain-Source Body Diode Characteristics						
Body Diode Forward Voltage	VSD	TJ = 25°C, ISD = 4A,VGS = 0V	--	0.9	1.4	V
Reverse Recovery Time	trr	VR = 400V, IF = 4A	--	220	--	ns
Reverse Recovery Charge	Qrr	diF/dt = 100A/μs	--	0.9	--	μC



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Notes:

1. $ISD \leq ID$, $di/dt \leq 200A/us$, $V_{DD} \leq BVDSS$, Starting $T_J = 25^\circ C$
2. Essentially Independent of Operating Temperature Typical Characteristics

■ TEST CIRCUITS AND WAVEFORMS

Figure A: Gate Charge Test Circuit and Waveform

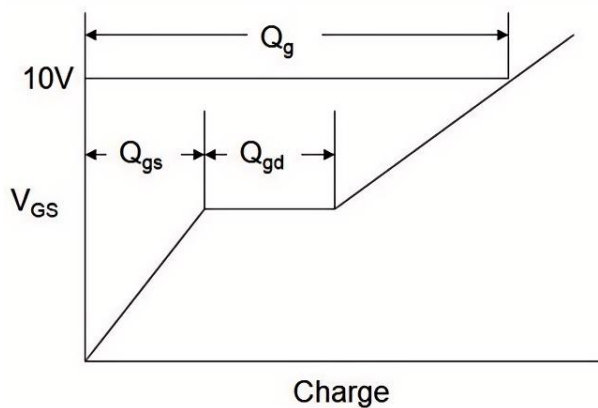
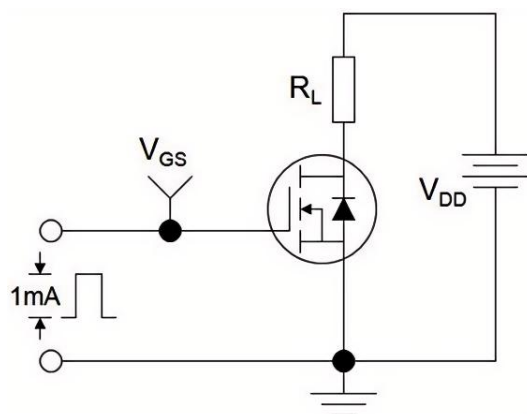


Figure B: Resistive Switching Test Circuit and Waveform

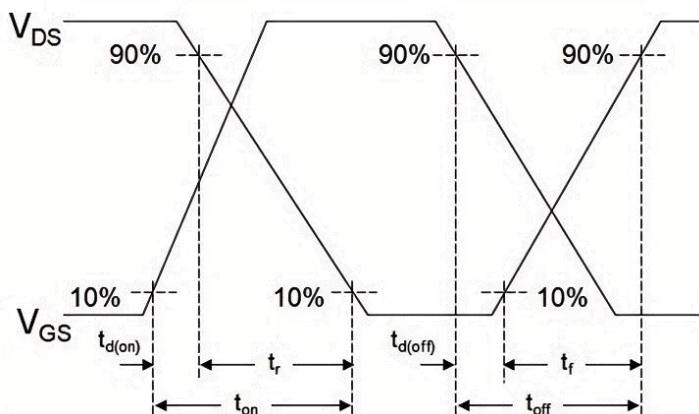
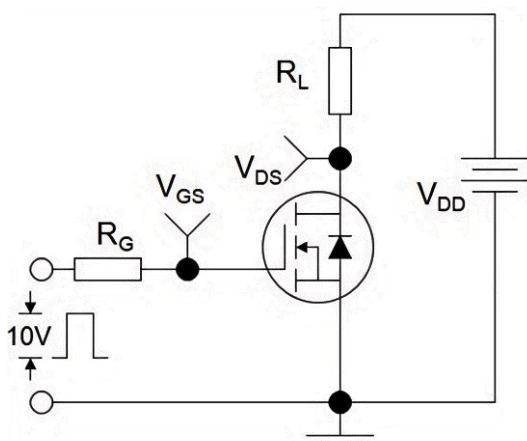
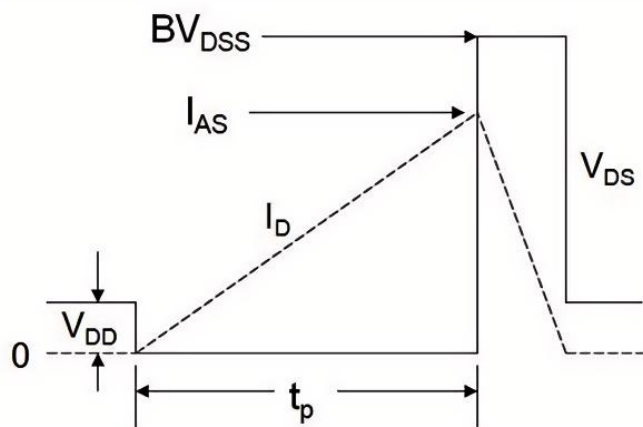
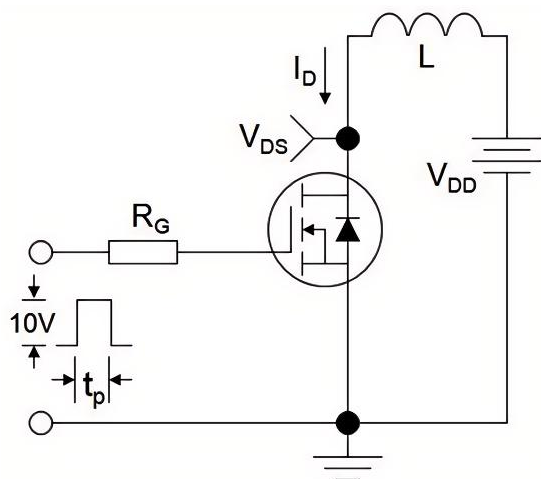


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





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TYPICAL CHARACTERISTICS

Figure 1. Output Characteristics

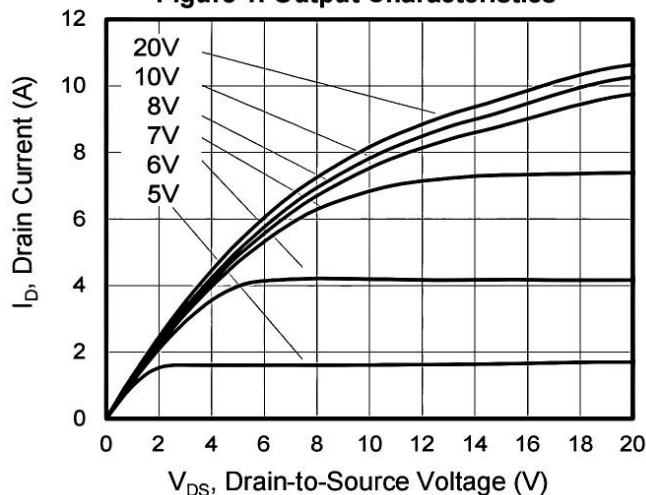


Figure 2. Transfer Characteristics

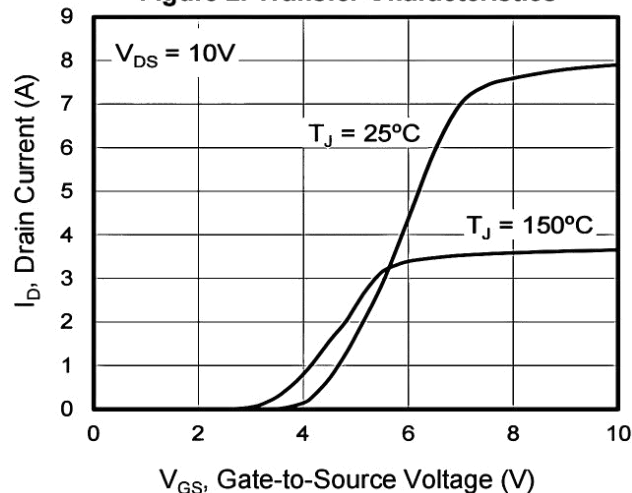


Figure 3. On-Resistance vs. Drain Current

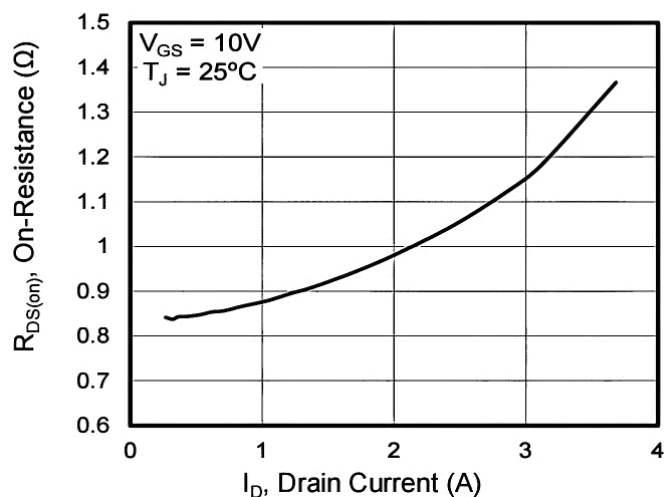


Figure 4. Capacitance

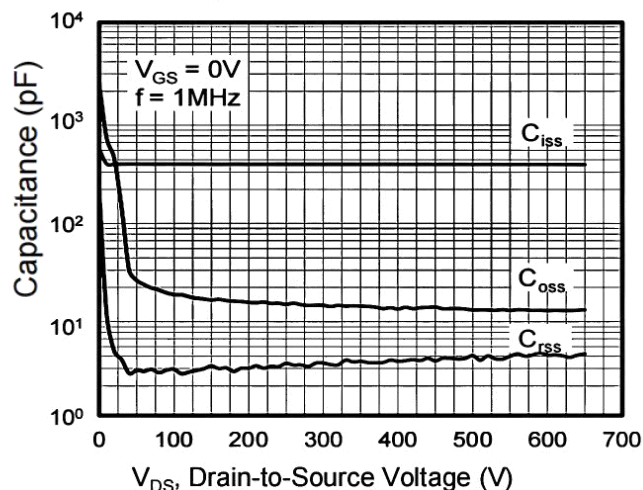


Figure 5. Gate Charge

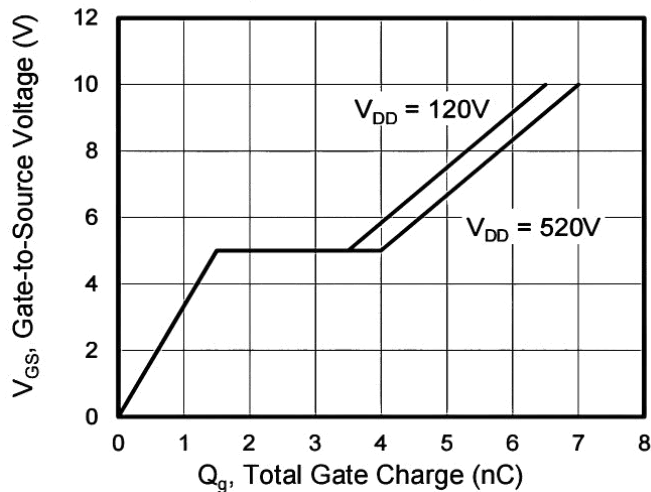
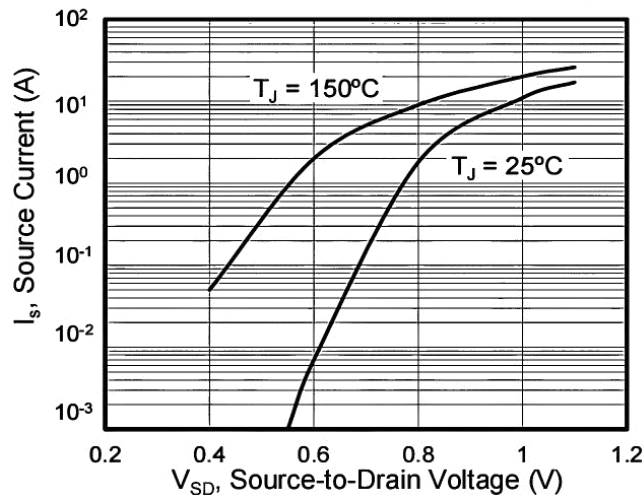


Figure 6. Body Diode Forward Voltage





■ TYPICAL CHARACTERISTICS(Con.t)

Figure 7. On-Resistance vs. Temperature

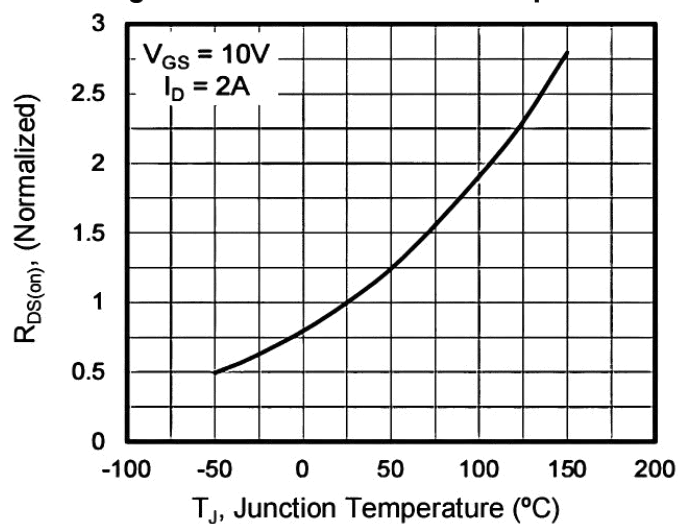


Figure 8. Breakdown Voltage vs. Junction Temperature

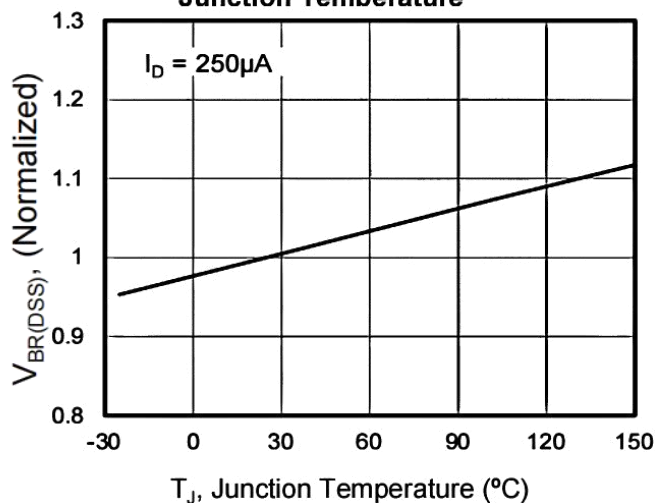


Figure 9. Transient Thermal Impedance TO-220F

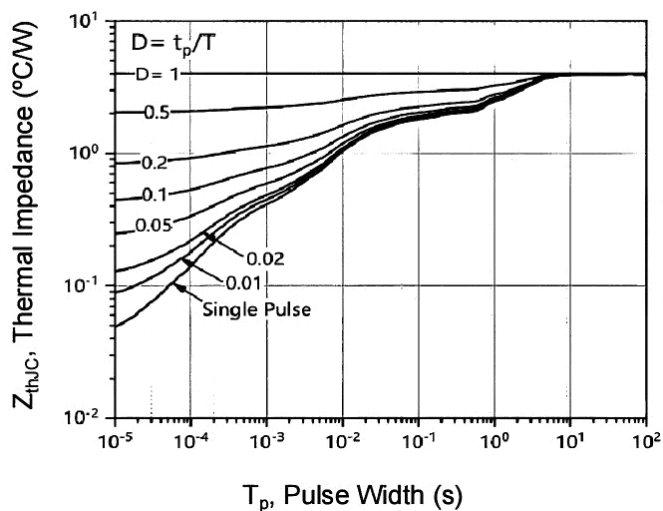
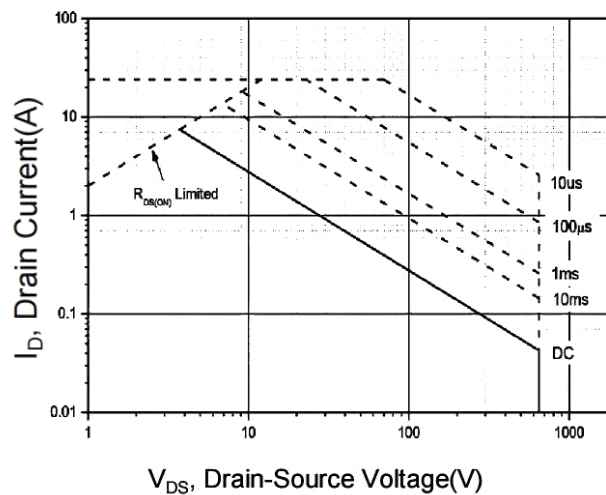


Figure 10. Safe Operation Area TO-220F

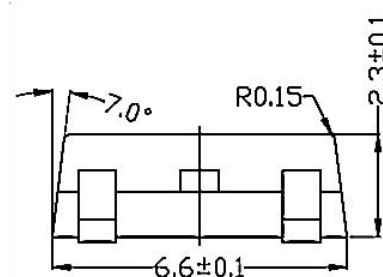
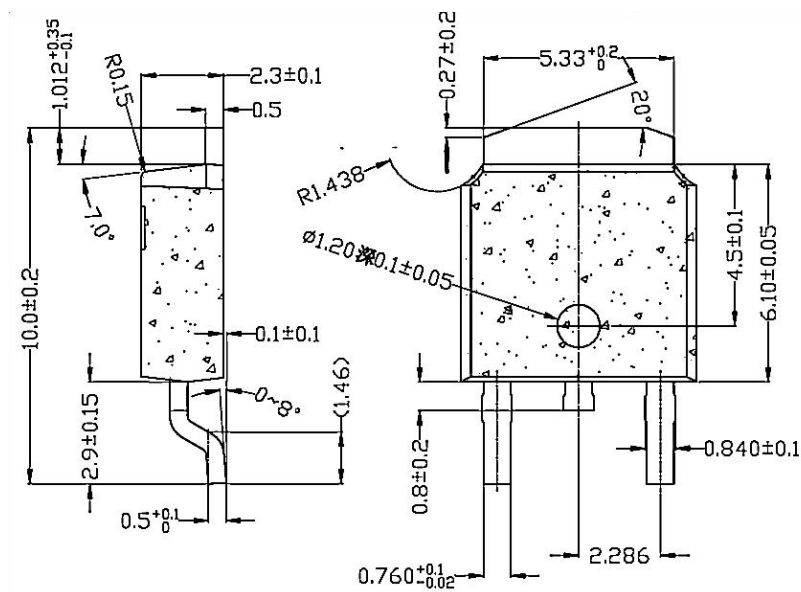




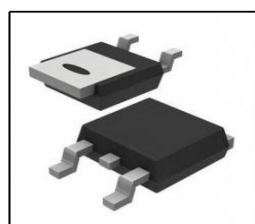
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TO - 252 PACKAGE OUTLINE DIMENSIONS



TO - 252 PACKING INFORMATION



2500PC
S/reel



2 Reel/BOX



Outer box

5 Inner
Box



Inner box

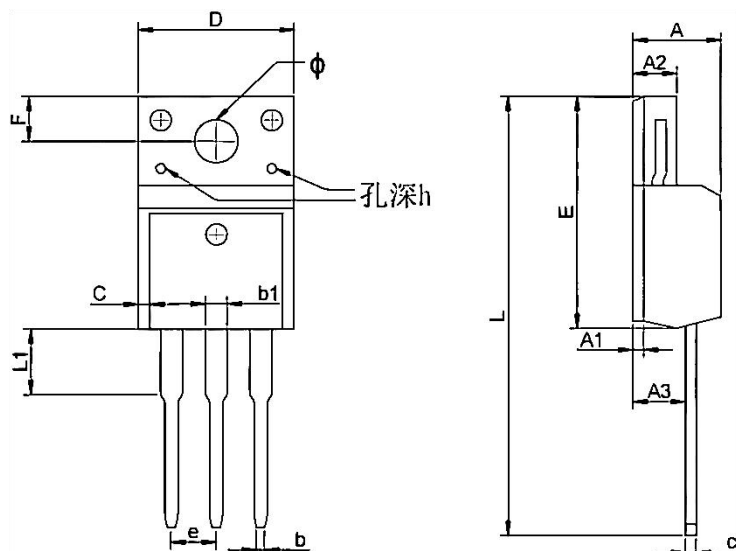
Package version	Reel dimensions $\Phi \times H$ (mm)	Per Reel (pcs)	Reels per box	Inner box dimensions $L \times W \times H$ (mm)	Outer box (pcs)	Outer box dimensions $L \times W \times H$ (mm)
TO-252	$\Phi 330 \times 20$	2500	2	360*340*50	25000	375*375*280



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TO- 220F PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.750	0.169	0.185
A1	1.830 REF		0.072 REF	
A2	2.300	2.850	0.090	0.112
A3	2.500	2.900	0.098	0.114
b	0.400	0.420	0.016	0.016
b1	1.220	1.280	0.048	0.050
C	0.690	0.720	0.027	0.028
c	0.490	0.510	0.019	0.020
D	9.960	10.200	0.392	0.400
E	15.000	15.950	0.588	0.625
e	2.574 TYP		0.101TYP	
F	3.470 REF		0.136 REF	
y	3.200 REF		0.125 REF	
h	0.000	0.300	0.000	0.012
L	28.780	28.900	1.128	1.133
L1	2.990	3.100	0.117	0.122

TO - 220F PACKING INFORMATION



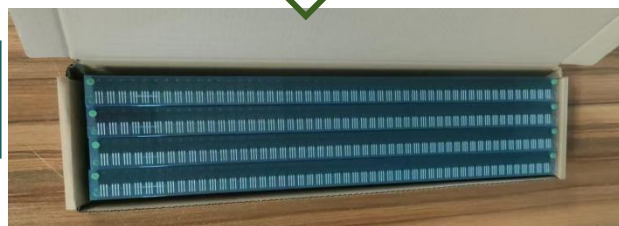
50PCS



20 Tube



5 Inner
Box



Outer Box

Inner Box

Package version	Tube dimensions LxWxH (mm)	Per Tube (pcs)	Tube per box	Inner box dimensions LxWxH (mm)	PCS/ Inner box	Outer box dimensions LxWxH(mm)	PCS/ Outer box
TO-220F	530*32*7	50	20	580*155*50	1000	602*277*188	5000